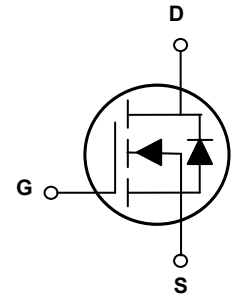
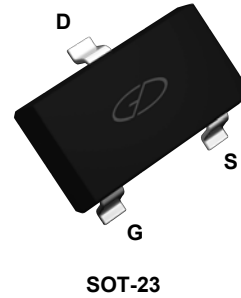


Main Product Characteristics

$V_{(BR)DSS}$	30V
$R_{DS(ON)(MAX)}$	31mΩ@10V
	43mΩ@4.5V
I_D	5.8A



Schematic Diagram

Features and Benefits

- Advanced MOSFET process technology
- Ideal for battery operated systems, load switching, power converters and other general purpose applications
- Low on-resistance with low gate charge
- Fast switching and reverse body recovery



Description

The GSF3404 utilizes the latest techniques to achieve high cell density and low on-resistance. These features make this device extremely efficient and reliable for use in high efficiency switch mode power supply and a wide variety of other applications.

Absolute Maximum Ratings ($T_A=25^{\circ}\text{C}$ unless otherwise specified)

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	30	V
Gate-Source Voltage	V_{GS}	±20	V
Drain Current-Continuous	I_D	5.8	A
Drain Current-Pulsed ¹	I_{DM}	20	A
Maximum Power Dissipation	P_D	1.4	W
Operating Junction and Storage Temperature	T_J, T_{STG}	-55 to +150	°C
Thermal Resistance from Junction to Ambient	$R_{\theta JA}$	89	°C/W

Electrical Characteristics ($T_A=25^\circ\text{C}$ unless otherwise specified)

Parameter	Symbol	Condition	Min	Typ	Max	Unit
Off Characteristics						
Drain-Source Breakdown Voltage	BV_{DSS}	$V_{GS}=0V, I_D=250\mu A$	30	33	-	V
Zero Gate Voltage Drain Current	I_{DSS}	$V_{DS}=30V, V_{GS}=0V$	-	-	1	μA
Gate-Body Leakage Current	I_{GSS}	$V_{GS}=\pm 20V, V_{DS}=0V$	-	-	± 100	nA
On Characteristics³						
Gate Threshold Voltage	$V_{GS(th)}$	$V_{DS}=V_{GS}, I_D=250\mu A$	1.0	1.5	2.0	V
Drain-Source On-State Resistance	$R_{DS(on)}$	$V_{GS}=10V, I_D=5A$	-	25.5	31	m Ω
		$V_{GS}=4.5V, I_D=4A$	-	36	45	m Ω
Forward Transconductance	g_{FS}	$V_{DS}=5V, I_D=5A$	-	15	-	S
Dynamic Characteristics						
Input Capacitance	C_{iss}	$V_{DS}=15V, V_{GS}=0V,$ $F=1.0\text{MHz}$	-	255	-	PF
Output Capacitance	C_{oss}		-	45	-	PF
Reverse Transfer Capacitance	C_{rss}		-	35	-	PF
Switching Characteristics						
Turn-on Delay Time	$t_{d(on)}$	$V_{DD}=15V, R_L=3\Omega$ $V_{GS}=10V, R_{GEN}=3\Omega$	-	4.5	-	nS
Turn-on Rise Time	t_r		-	2.5	-	nS
Turn-Off Delay Time	$t_{d(off)}$		-	14.5	-	nS
Turn-Off Fall Time	t_f		-	3.5	-	nS
Total Gate Charge	Q_g	$V_{DS}=15V, I_D=5A,$ $V_{GS}=10V$	-	5.2	-	nC
Gate-Source Charge	Q_{gs}		-	0.85	-	nC
Gate-Drain Charge	Q_{gd}		-	1.3	-	nC
Drain-Source Diode Characteristics						
Diode Forward Voltage ³	V_{SD}	$V_{GS}=0V, I_S=5A$	-	-	1.2	V
Diode Forward Current ²	I_S		-	-	5	A

Notes:

1. Repetitive Rating: Pulse width limited by maximum junction temperature.
2. Surface Mounted on FR4 Board, $t \leq 10$ sec.
3. Pulse Test: Pulse Width $\leq 300\mu s$, Duty Cycle $\leq 2\%$.

Typical Electrical and Thermal Characteristic Curves

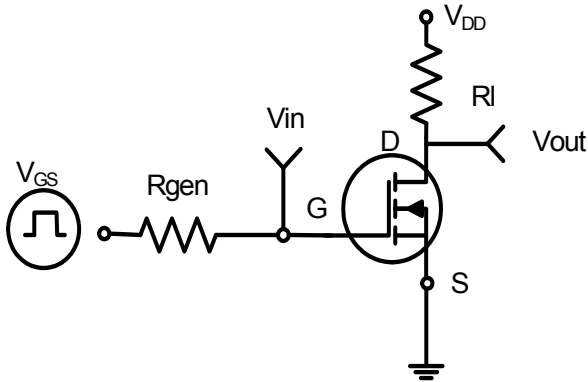


Figure 1 Switching Test Circuit

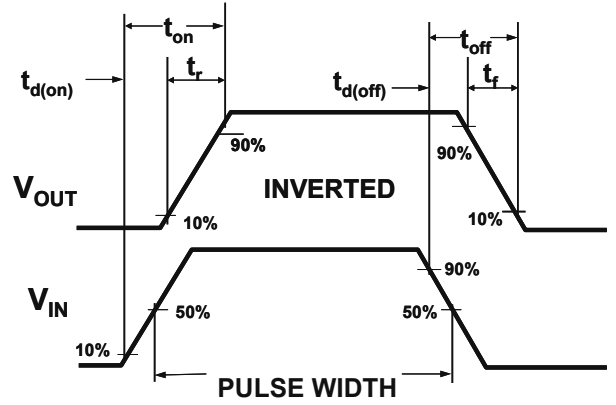


Figure 2 Switching Waveforms

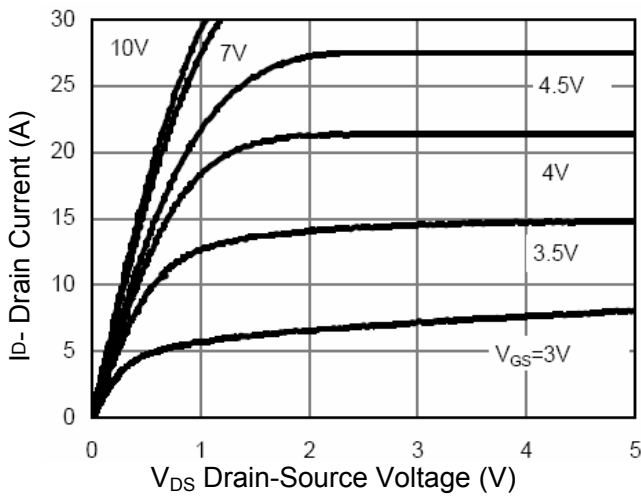


Figure 3 Output Characteristics

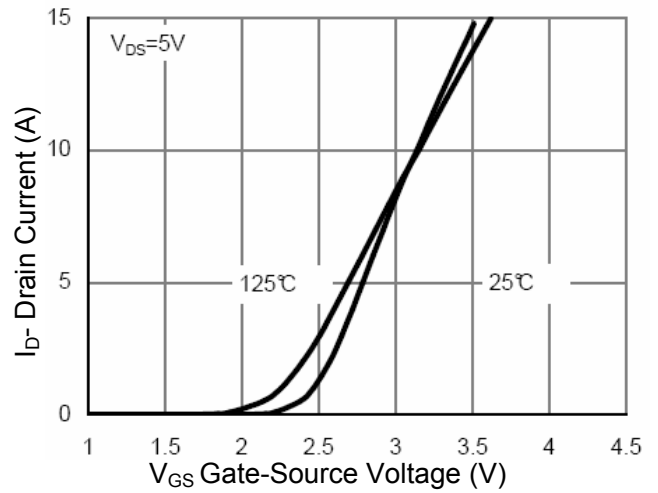


Figure 4 Transfer Characteristics

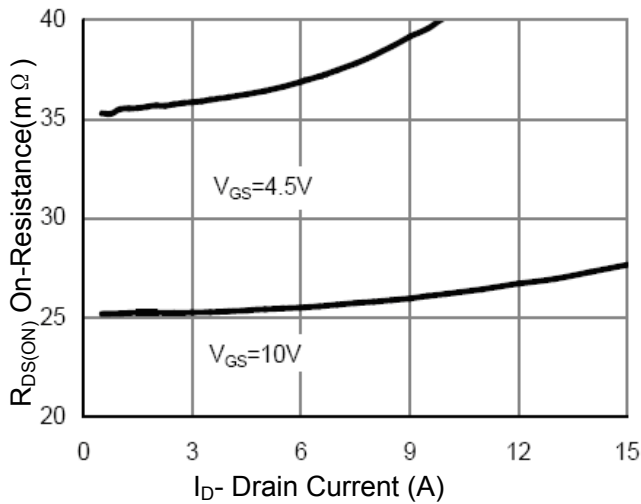


Figure 5 Drain-Source On-Resistance

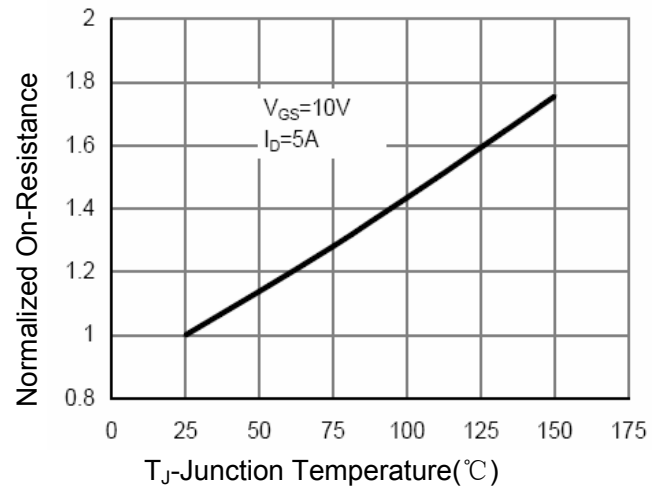


Figure 6 Drain-Source On-Resistance

Typical Electrical and Thermal Characteristic Curves

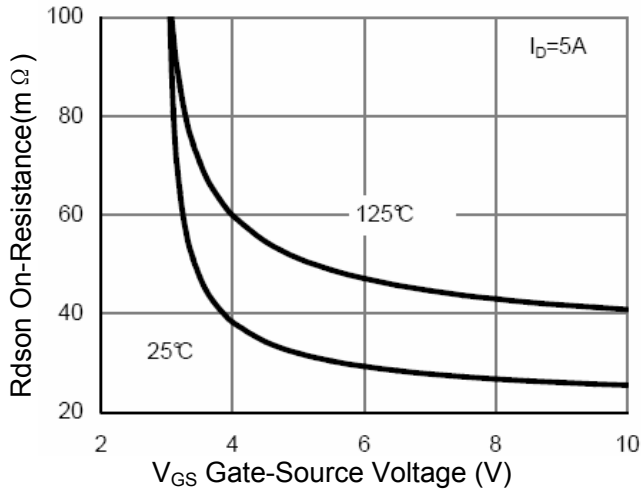


Figure 7 $R_{DS(ON)}$ vs V_{GS}

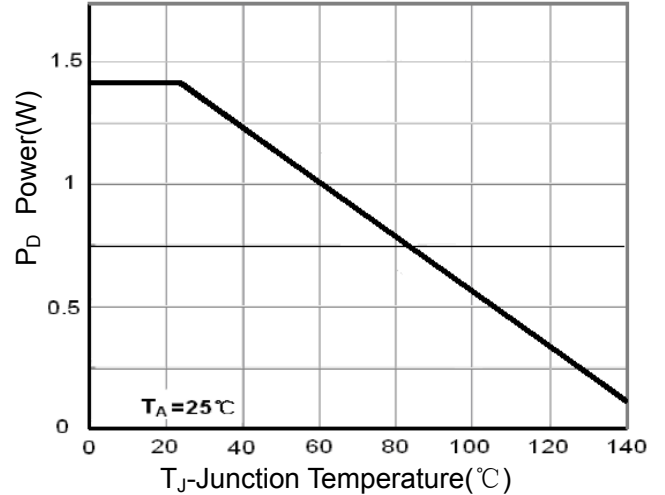


Figure 8 Power Dissipation

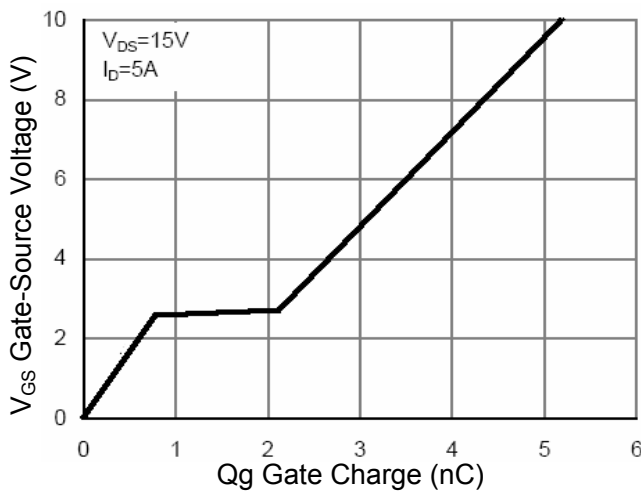


Figure 9 Gate Charge

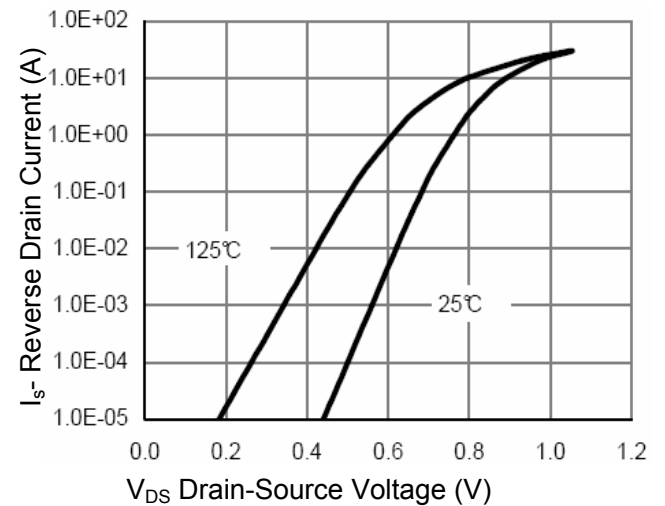


Figure 10 Source-Drain Diode Forward

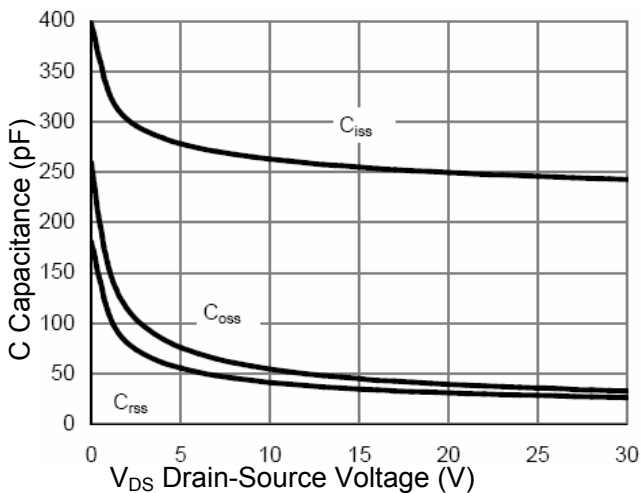


Figure 11 Capacitance vs V_{ds}

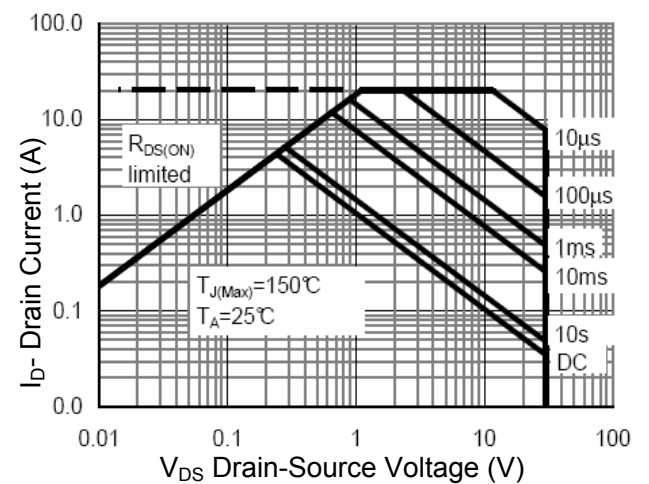


Figure 12 Safe Operation Area

Typical Electrical and Thermal Characteristic Curves

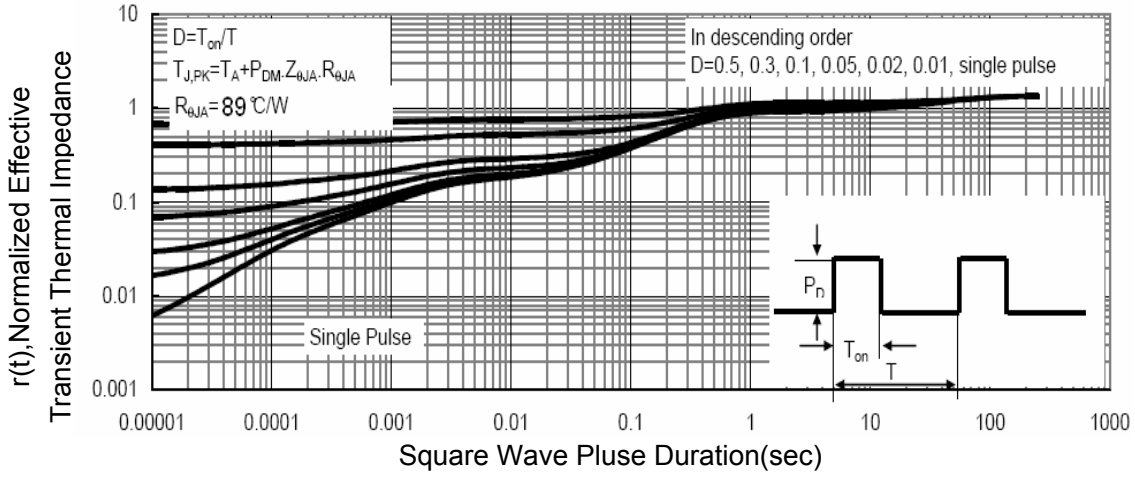
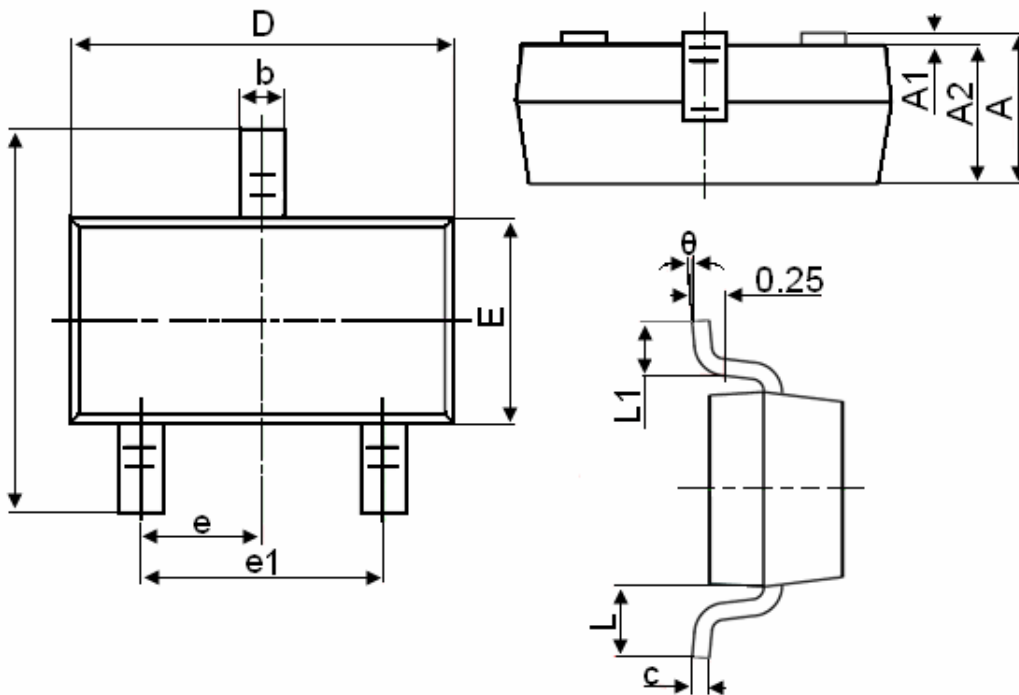


Figure 13 Normalized Maximum Transient Thermal Impedance

Package Outline Dimensions

SOT-23



Symbol	Dimensions In Millimeters		Dimensions In Inches	
	Min.	Max.	Min.	Max.
A	0.900	1.150	0.035	0.045
A1	0.000	0.100	0.000	0.004
A2	0.900	1.050	0.035	0.041
b	0.300	0.500	0.012	0.020
c	0.080	0.150	0.003	0.006
D	2.800	3.000	0.110	0.118
E	1.200	1.400	0.047	0.055
E1	2.250	2.550	0.089	0.100
e	0.950 TYP.		0.037 TYP.	
e1	1.800	2.000	0.071	0.079
L	0.550 REF.		0.022 REF.	
L1	0.300	0.500	0.012	0.020
θ	0°	8°	0°	8°